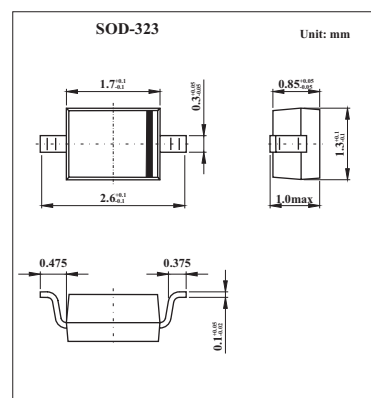


Silicon Schottky diode

BAT15-03W

■ Features

- DBC mixer applications to 12 GHz
- Low noise figure
- Low barrier type

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Value	Unit
Diode reverse voltage	V_R	4	V
Forward current	I_F	100	mA
Total power dissipation $T_s = 70^\circ\text{C}$	P_{tot}	100	mW
Operating temperature range	T_{op}	-55 to +150	°C
Storage temperature	T_{stg}	-55 to +150	
Junction ambient ⁽¹⁾	R_{thJA}	≤ 770	K/W
Junction-soldering point	R_{thJS}	≤ 690	K/W

Note:

1. Package mounted on an epoxy pcb 40 mm × 40 mm × 15 mm/1cm² Cu.

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min	Typ	Max	Unit
Breakdown Voltage $I_{(BR)} = 5\mu\text{A}$	$V_{(BR)}$	4			V
Forward voltage $I_F = 1\text{ mA}$ $I_F = 10\text{ mA}$	V_F		0.23 0.32	0.32 0.41	V
Diode capacitance $V_R = 0; f = 1\text{ MHz}$	C_T			0.35	pF
Differential forward resistance $I_F = 10\text{ mA}/50\text{ mA}$	R_F		5.5		Ω

■ Marking

Marking	P
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